

Gain and Stability Behaviour of Carbon Coated GEMs

RD51 Mini-Week
CERN

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1 Introduction

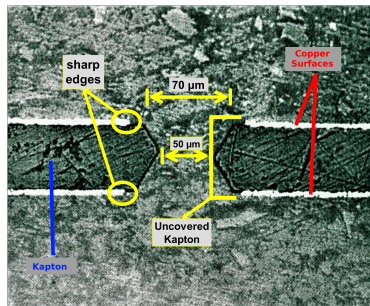
- Diamond Like Carbon (DLC) Coated GEM
- Coating Procedure

2 Measurements

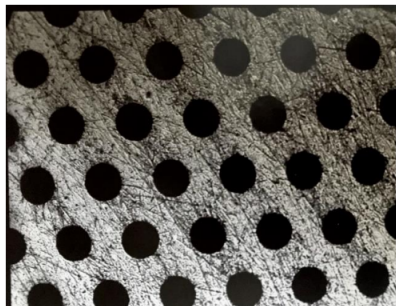
- AFM Analysis
- Gain of DLC GEMs
- Environmental Parameters
- Turn on effect

3 Summary

- Motivation
 - ▶ Reduce of **discharge probability** by coating **sharp edges** and **kapton** inside the holes
 - ▶ Establishment of **well defined electric field within the hole**
 - ▶ Increase of **maximum safe gain voltage** (and gain)
- Three batches of coating with different thicknesses
 - ▶ **50 nm**, **100 nm**, **300 nm**



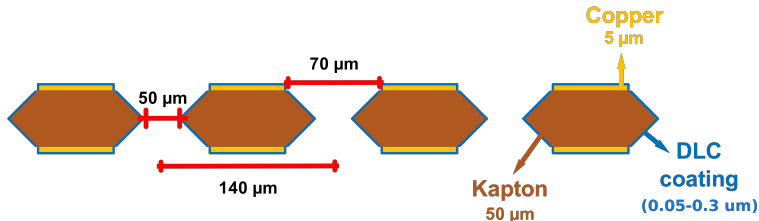
Cross section of a GEM*



Surface of a DLC GEM*

- Coatings done by **Fraunhofer Institut für Oberflächentechnik** using Plasma assisted Chemical Vapor Deposition (PACVD) procedure.
 - In a vacuum chamber
 - Hexamethyldisiloxane (HMDSO)** for **a-C:H:Si:O (SICON)** coating
 - High electric field to break HMDSO into fragments
- Thickness control by deposition time

Coating material	Chemical deposition	Element Concentration			
		C	H	Si	O
HMDSO	a-C:H:Si:O	41-43	22-23	23-24	10-11

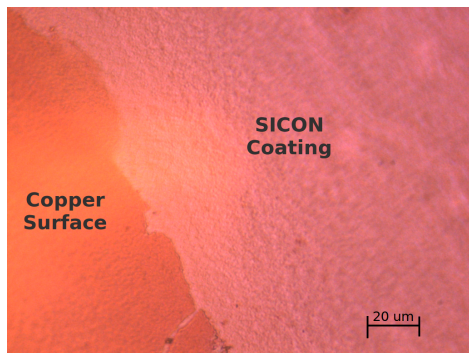


Schematic Cross section of a DLC GEM*

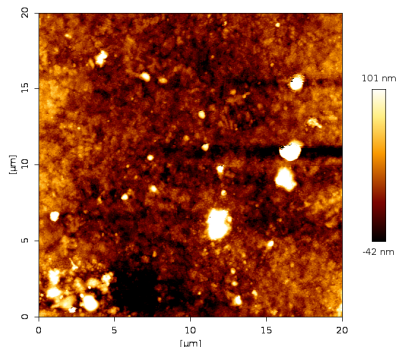
*A. Alfarrá, Master Thesis, October 2018

AFM Analysis (Preliminary)

- Samples for analysis
 - ▶ **Additional coated GEMs** in the same coating process of DLC GEMs for AFM analysis
 - ▶ Coating **roughness is ~5-10nm**
 - ▶ Coating **thickness** measurement is under study



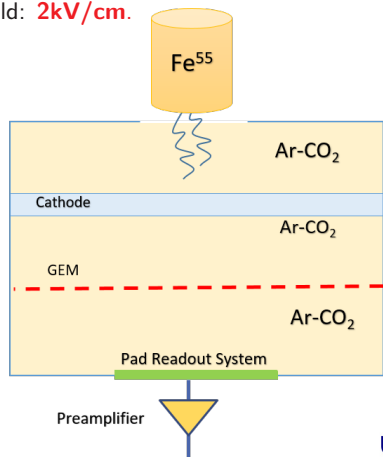
Surface of a 50nm SICON GEM



AFM picture of 50nm sicon GEM surface

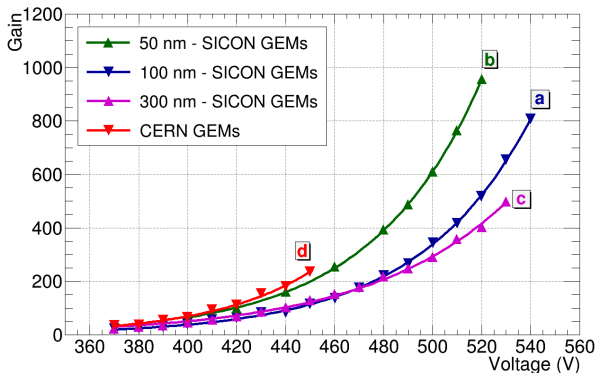
- Motivation: **Smaller drift distance, higher drift fields.**
- Small chamber (**120 mm × 184 mm**) to measure the gain of GEMs.
- Gas mixture: **Ar – CO₂ (80% – 20%)** mixture.
- 5.9 keV **X-ray source (⁵⁵Fe)** for primary ionization.
- Drift field: **0.5 kV/cm**, induction field: **2kV/cm.**
- Pressure: **Absolute air pressure**
- Temperature: **Room temperature**

A scheme of the arrangement
of the GEM inside the test
chamber*



*Amir Alfara.

Gain
comparison of
all coated and
CERN GEMs*



- Gains corrected to **1 atm** and **300K** by coefficients from Garfield++ simulation
- **Lower gain at same voltage** for coated GEMs
- Highest gain (**>1000 w/o correction**) with **50nm coated GEMs**.
- **The thicker the thickness, the lower the gain** at same voltage.
- Maximum safe gain voltage for all coated GEMs: **510V**

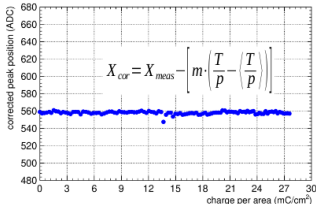
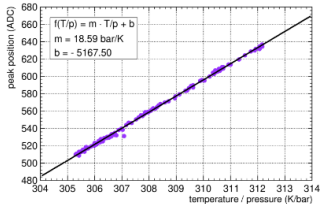
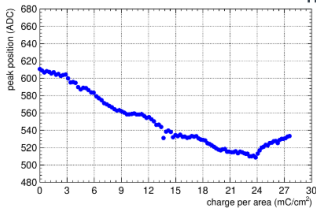
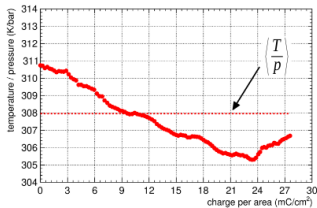
*A. Alfara, Master Thesis, October 2018

- Environmental parameter correction: **Simulations** → **Measurements**

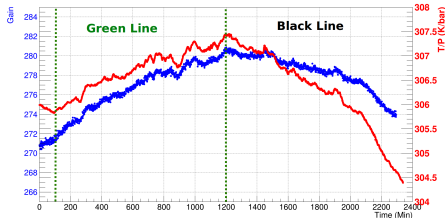
Influence of temperature and pressure conditions



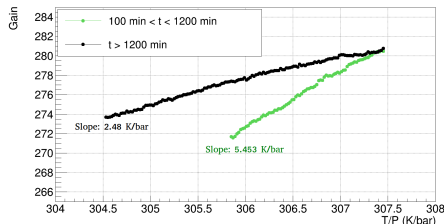
ALICE



- All measured currents and the peak position are corrected with this procedure

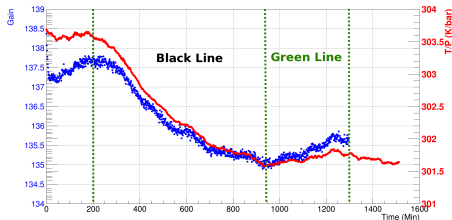


100nm SICON GEM @480V

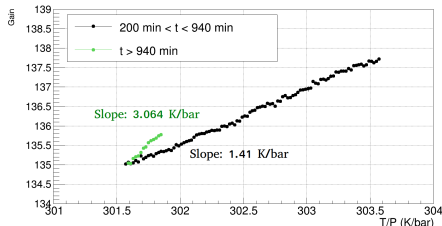


100nm SICON GEM @480V

- Results from **100nm SICON GEM @480V**
- 2 different slopes depending on T/P trend.
 - ▶ **Low slope when T/P decreases**
 - ▶ **High slope when T/P increases**
- Why different slopes of T/P vs. gain?

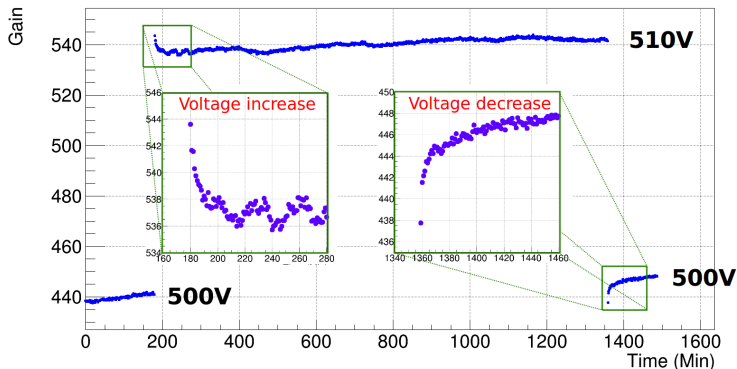


CERN GEM @430V



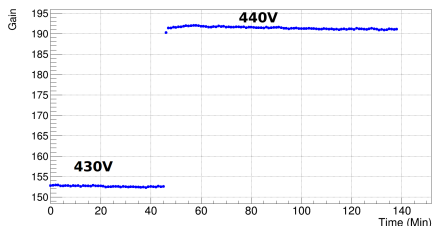
CERN GEM @430V

- Results from **CERN GEM @430V**
- 2 different slopes depending on T/P trend.
 - ▶ **Low slope when T/P decreases**
 - ▶ **High slope when T/P increases**
- Why different slopes of T/P vs. gain?

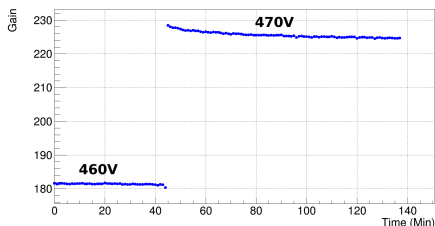


Gain during voltage change 100nm SICON GEM

- Each point is 1 minute of spectrum
- When voltage is
 - ▶ increased, **gain increases higher than its new equilibrium** then stabilizes.
 - ▶ decreased, **gain decreases lower than its new equilibrium** then stabilizes.
- Is this behaviour expected for GEMs?



CERN GEM



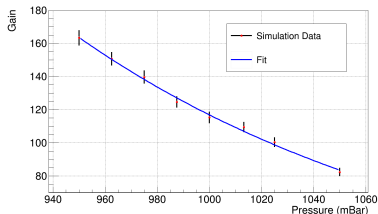
100nm SICON GEM

- Turn on effect comparison for **CERN GEM** and **100nm SICON GEM** after voltage change
- **CERN GEM doesn't have** turn on effect
- **SICON GEM has turn on effect $\sim 2\%$** for 10V change

- CERN GEMs have been DLC coated by PACVD method with 3 different thicknesses **(50nm, 100nm, 300nm)**.
- **Roughness is ~5-10nm.**
- **Thickness measurement** of coatings is under investigation.
- With DLC coating, **lower gain is achieved at same voltage**, but **higher voltages are accessible to reach x5 gain than in CERN GEM.**
- **The thicker the coating, the lower the gain at same voltage.**
- Environmental parameters (temperature and pressure) **affect the gain differently** (even for CERN GEMs) during increase and decrease of T/P. Gain changes slower when T/P is decreasing.
- After voltage change, **gain of the SICON GEM instantly overshoots and undershoots, then stabilizes.**

Backup

- Assumption for gain adjustment:
 - $G = e^{\alpha x}$ is valid
 - $\alpha = Ape^{-Bp/E} \propto p$ is valid
- Pressure adjustment fit function: $G = e^{sp+c}$
 - s: slope
 - c: constant

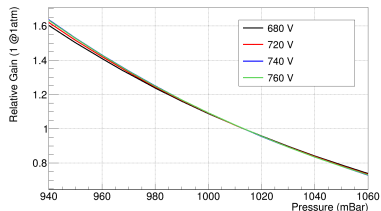


Fit on simulations of ceramic GEM at 740 V

- Gain adjustment (at 1 atm):

$$G_{corr} = \frac{G_{meas}(p)}{e^{sp+c}}$$

V_{GEM} (V)	slope (Bar^{-1})	constant
680	$-6.44 \pm 4.5\%$	$6.53 \pm 4.5\%$
720	$-6.59 \pm 4.4\%$	$6.68 \pm 4.4\%$
740	$-6.72 \pm 4.5\%$	$6.81 \pm 4.5\%$
760	$-6.69 \pm 4.8\%$	$6.78 \pm 4.8\%$



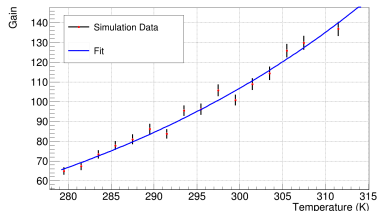
Fits on simulations of ceramic GEM at different V_{GEM}

- Adjustment function by fitting simulation data
- Temperature adjustment fit function: $G = e^{sT+c}$
 - ▶ s: slope
 - ▶ c: constant

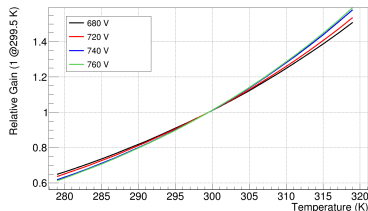
- Gain adjustment (at 299.5 K):

$$G_{corr} = \frac{G_{meas}(T)}{e^{sT+c}}$$

V_{GEM} (V)	slope ($10^2 K^{-1}$)	constant
680	$2.11 \pm 2.2\%$	$-6.32 \pm 2.2\%$
720	$2.2 \pm 2.1\%$	$-6.59 \pm 2.1\%$
740	$2.35 \pm 3\%$	$-7.03 \pm 3\%$
760	$2.39 \pm 5.4\%$	$-7.15 \pm 5.4\%$



Fit on simulations of ceramic GEM
at 740 V



Fits on simulations of ceramic
GEM at different V_{GEM}

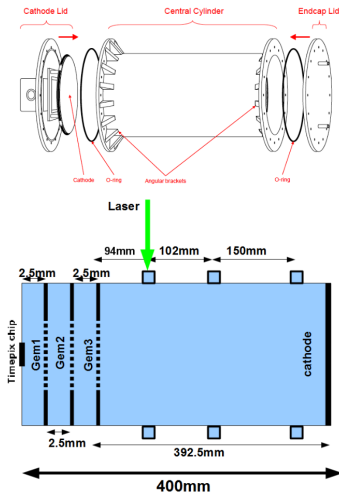
- The gas system includes a gas mixing system with desired percentages and a small chamber to monitor gas stabilization inside the experimental chamber
- After mixing process, gas mixture flows through the test chamber and/or the TPC prototype
- Later, the gas mixture flows to another chamber where we can monitor gas stabilization before it is released to air.



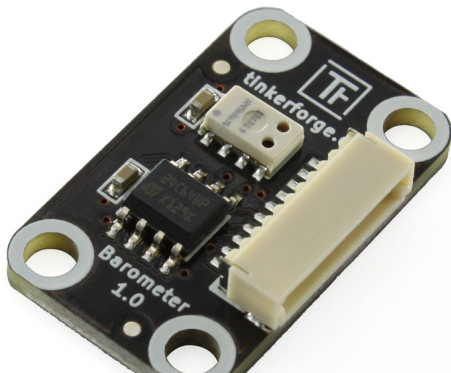
TPC Prototype in Siegen

In Siegen we have a cylindrical TPC prototype with 240mm diameter and 400mm length

- As readout detector, it has a TimePix chip which has 256×256 pixel resolution with $55\mu\text{m} \times 55\mu\text{m}$ pixel size
- The TimePix chip is controlled via FPGA card and signal is recorded in a matrix form which includes possible tracks of electrons
- To be able to start primary ionization, a UV laser and beta-ray source are used in 3 entry holes.



- Pressure of the gas mixture is slightly higher than absolute air pressure.
- Thus, absolute air pressure can be used as gas pressure since pressure difference is negligible
- Absolute air pressure is measured by a pressure sensor (MS5611-01BA01)
- Temperature is measured built-in temperature sensor of the pressure sensor

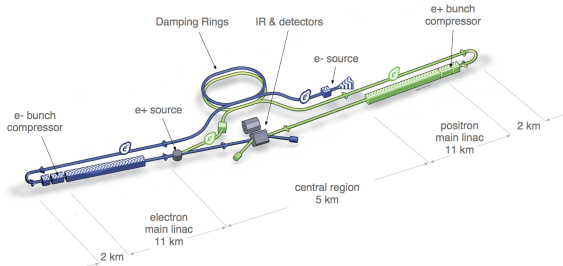


International Linear Collider (ILC)

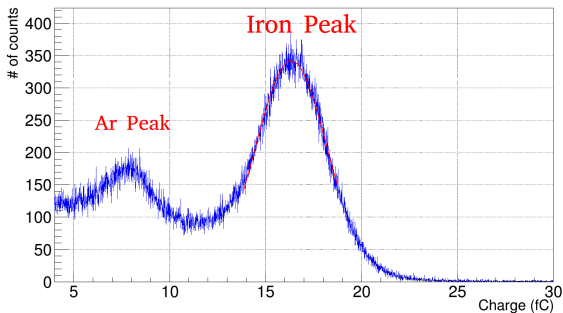


A Time Projection Chamber
for a Future Linear Collider

- **Electron - positron** collider
- Foreseen length: **31 km***
- Center of mass energy: **250 GeV to 500 GeV (1 TeV)**
- Two foreseen detectors, one of them being the International Large Detector (ILD)
- Time Projection Chamber (TPC) as the tracker for the ILD
 - ▶ One of the candidates for electron multiplication: Gas electron multiplier (GEM)



*R. Diener, *Physics Procedia*, 00 (2012) 1-8



Signal with 2 peaks (Argon escape peak and ^{55}Fe peak).

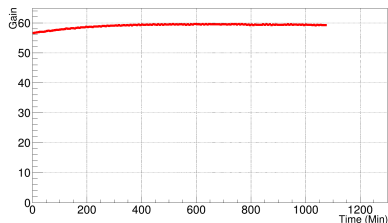
- Number of primary electrons:

$$n_p = \frac{5900 \text{ eV}}{26 \text{ eV}} \times 0.80 + \frac{5900 \text{ eV}}{34 \text{ eV}} \times 0.20 = 216$$

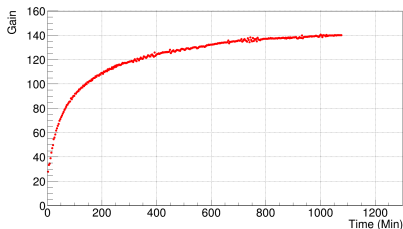
▶ 26eV and 34eV : Average energy per ionization for *Ar* and CO_2 respectively.

- Thus, the gain: ratio of total (n_t) to primary (n_p) electron number

$$G = n_t \times \frac{1}{n_p} = \frac{Q_t}{e} \times \frac{1}{216}$$



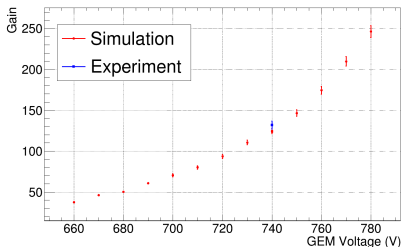
Long time measurement with
CERN GEM at $V_{GEM}=390$ V.



Long time measurement with
ceramic GEM at $V_{GEM}=740$ V.

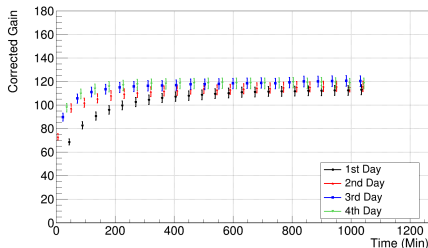
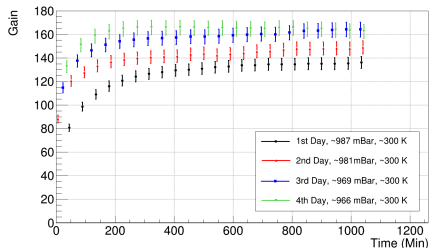
- The first important result of ceramic GEM: **Charge up effect.**
 - ▶ CERN GEM gain starts already from **95% of maximum gain**
 - ▶ Gain stabilization of a ceramic GEM takes **hours.**

- Field maps from ANSYS.
- Simulation with GEM specifications and geometries.
- Agreement within uncertainties (for the gains after stabilization)
- Pressure and temperature adjustment to compare measurements



V_{GEM} vs. gain for ceramic GEM

GEM	data	V_{GEM} (V)	P (Bar)	T (K)	Gain	G_{sim}/G_{meas}
CERN	experiment	390	0.987	298	59.64 ± 2.17	
CERN	simulation	390	0.987	298	60.56 ± 1.15	1.015 ± 0.056
Ceramic	experiment	740	0.9875	299.5	131.2 ± 4.91	
Ceramic	simulation	740	0.9875	299.5	124.6 ± 3.13	0.95 ± 0.059

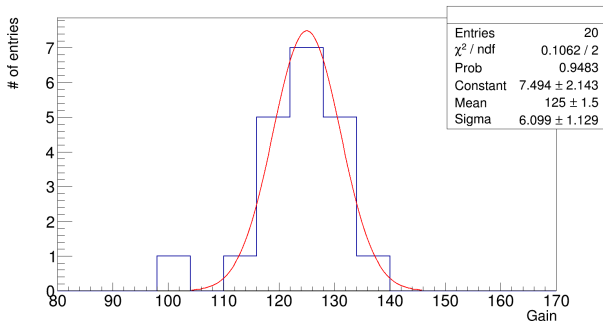


Long time measurements **before adjustment** for 4 consecutive days with ceramic GEM at 740 V.

Long time measurements **after adjustment** at 740 V, 1 atm and 299.5 K.

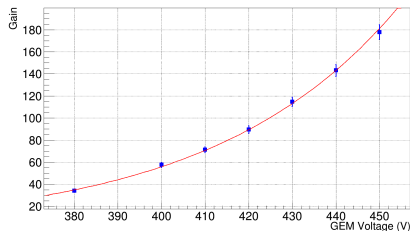
Time required for	1st Day	2nd Day	3rd Day	4th Day	3 Days Later
90% of max gain	258 min	132 min	93 min	69 min	189 min
95% of max gain	414 min	276 min	192 min	117 min	297 min

- Pressure and temperature adjusted to **1 atm** and **299.5 K**,
- Second important result: **Conditioning**
 - ▶ Increase of gain stabilization with consecutive measurements

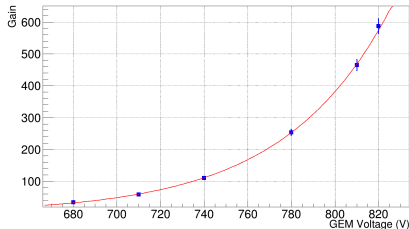


Distribution of gains from different measurements taken for 4 months of period

- Mean of the distribution of the adjusted gains (at 1 atm and 299.5 K) from different measurements: **125**
- Variation within 68% inclusion area: $\sigma/\mu = 4.9\%$



CERN GEM voltage vs gain.
976 mBar and 301-302 K



Ceramic GEM voltage vs gain.
982-985 mBar and 300-301 K

- Achievable maximum voltage without discharges
 - ▶ for CERN GEM: **450 V**
 - ▶ for ceramic GEM: **820 V**
- Gain at achievable voltage without discharges
 - ▶ for CERN GEM: **178**
 - ▶ for ceramic GEM: **586**

- Long time stability measurements
 - ▶ Operation stability
 - ▶ Gain stability
- Repeatability of measurements
 - ▶ Comparison of measurements
 - ★ Challenges in comparison due to varying pressure and temperature
 - ★ Adjustment of the gain to a chosen pressure and temperature using Garfield++ simulation data
- Achievable maximum voltage and gain